

گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما



09153223758





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مشهد خیام شمالی 63 خیابان پردیس 3

برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش
 تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
 - آموزش تخصصی ابراز آلات شارژی



Single Supply Dual **Operational Amplifiers**

LM258, LM358, LM358A, LM358E, LM2904, LM2904A, LM2904E, LM2904V, NCV2904

Utilizing the circuit designs perfected for Quad Operational Amplifiers, these dual operational amplifiers feature low power drain, a common mode input voltage range extending to ground/V_{EE}, and single supply or split supply operation. The LM358 series is equivalent to one-half of an LM324.

These amplifiers have several distinct advantages over standard operational amplifier types in single supply applications. They can operate at supply voltages as low as 3.0 V or as high as 32 V, with

quiescent currents about one-fifth of those associated with the MC1741 (on a per amplifier basis). The common mode input range includes the negative supply, thereby eliminating the necessity for

external biasing components in many applications. The output voltage range also includes the negative power supply voltage.

Features

- Short Circuit Protected Outputs
- True Differential Input Stage
- Single Supply Operation: 3.0 V to 32 V
- Low Input Bias Currents
- Internally Compensated
- Common Mode Range Extends to Negative Supply
- Single and Split Supply Operation
- ESD Clamps on the Inputs Increase Ruggedness of the Device without Affecting Operation
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



PDIP-8 N, AN, VN SUFFIX **CASE 626**

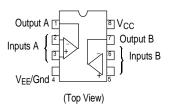


SOIC-8 D, VD SUFFIX **CASE 751**



Micro8™ **DMR2 SUFFIX CASE 846A**

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 11 of this data sheet.

$LM258,\,LM358A,\,LM358E,\,LM2904,\,LM2904A,\,LM2904E,\,LM2904V,\,NCV2904$



Figure 1.

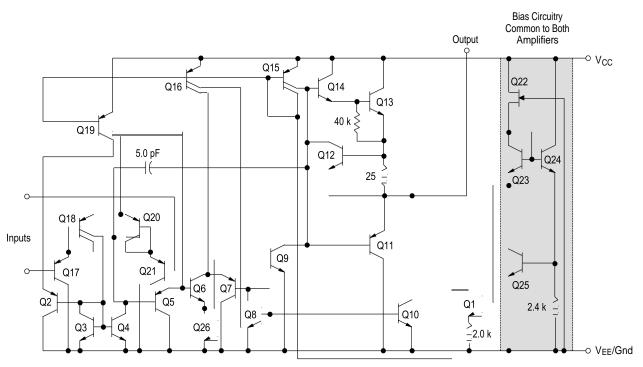


Figure 2. Representative Schematic Diagram (One–Half of Circuit Shown)

MAXIMUM RATINGS ($T_A = +25$ °C, unless otherwise noted.)

Rating		Symbol	Value	Unit
Power Supply Voltages Single Supply Split Supplies		V _{CC} , V _{EE}	32 ±16	Vdc
Input Differential Voltage Range (Note 1)		V_{IDR}	±32	Vdc
Input Common Mode Voltage Range		V _{ICR}	−0.3 to 32	Vdc
Output Short Circuit Duration		t _{SC}	Continuous	
Junction Temperature		T _J	150	°C
Thermal Resistance, Junction-to-Air (Note 2)	Case 846A Case 751 Case 626	$R_{ hetaJA}$	238 212 161	°C/W
Thermal Resistance, Junction-to-Case	Case 751	$R_{ heta JC}$	72	°C/W
Thermal Resistance, Junction-to-Board	Case 751	$R_{\theta JB}$	74	°C/W
Storage Temperature Range		T _{stg}	−65 to +150	°C
LM2904,	LM258 3, LM358A, LM358E LM2904A, LM2904E /, NCV2904 (Note 3)	T _A	-25 to +85 0 to +70 -40 to +105 -40 to +125	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Split Power Supplies.

ESD RATINGS

Rating	НВМ	ММ	Unit
ESD Protection at any Pin (Human Body Model – HBM, Machine Model – MM)			
NCV2904 (Note 3)	2000	200	V
LM358E, LM2904E	2000	200	V
LM358DG/DR2G, LM2904DG/DR2G	250	100	V
All Other Devices	2000	200	V

^{2.} All $R_{\theta JA}$ measurements made on evaluation board with 1 oz. copper traces of minimum pad size. All device outputs were active. 3. NCV2904 is qualified for automotive use.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ V}$, $V_{EE} = GND$, $T_A = 25^{\circ}C$, unless otherwise noted.)

			LM258		LM3	58, LM3	358E		_M358 <i>A</i>	4	
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Input Offset Voltage $ \begin{array}{l} V_{CC} = 5.0 \text{ V to } 30 \text{ V, } V_{IC} = 0 \text{ V to } V_{CC} - 1.7 \text{ V,} \\ V_O \ 1.4 \text{ V, } R_S = 0 \ \Omega \end{array} $	V _{IO}										mV
$T_A = 25$ °C $T_A = T_{high}$ (Note 4) $T_A = T_{low}$ (Note 4)		- - -	2.0 - -	5.0 7.0 7.0	- - -	2.0 - -	7.0 9.0 9.0	- - -	2.0 - -	3.0 5.0 5.0	
Average Temperature Coefficient of Input Offset Voltage	ΔV _{IO} /ΔΤ	-	7.0	-	-	7.0	-	-	7.0	-	μV/°C
T _A = T _{high} to T _{low} (Note 4)	T		2.0	20						20	
Input Offset Current $T_A = T_{high}$ to T_{low} (Note 4) Input Bias Current $T_A = T_{high}$ to T_{low} (Note 4)	I _{IB}	- - -	3.0 - -45 -50	30 100 -150 -300	- - -	5.0 - -45 -50	50 150 -250 -500	- - -	5.0 - -45 -50	30 75 -100 -200	nA
Average Temperature Coefficient of Input Offset Current TA = Thigh to Tlow (Note 4)	ΔΙ _{ΙΟ} /ΔΤ	-	10	-	-	10	-	-	10	-	pA/°C
Input Common Mode Voltage Range (Note 5), V _{CC} = 30 V	V _{ICR}	0	-	28.3	0	-	28.3	0	-	28.5	V
$V_{CC} = 30 \text{ V}, T_A = T_{high} \text{ to } T_{low}$		0	-	28	0	-	28	0	-	28	
Differential Input Voltage Range	V_{IDR}	-	-	V_{CC}	-	-	V_{CC}	-	-	V_{CC}	V
Large Signal Open Loop Voltage Gain $R_L = 2.0 \text{ k}\Omega$, $V_{CC} = 15 \text{ V}$, For Large Vo Swing, $T_A = T_{high} \text{ to } T_{low} \text{ (Note 4)}$	A _{VOL}	50 25	100 -		25 15	100 -	1 1	25 15	100 -	-	V/mV
Channel Separation $1.0 \text{ kHz} \leq f \leq 20 \text{ kHz, Input Referenced}$	CS	-	-120	-	-	-120	-	-	-120	-	dB
Common Mode Rejection $R_S \leq 10 \ k\Omega$	CMR	70	85	-	65	70	-	65	70	-	dB
Power Supply Rejection	PSR	65	100	-	65	100	-	65	100	-	dB
Output Voltage–High Limit $T_A = T_{high} \text{ to } T_{low} \text{ (Note 4)}$ $V_{CC} = 5.0 \text{ V, } R_L = 2.0 \text{ k}\Omega, T_A = 25^{\circ}\text{C}$ $V_{CC} = 30 \text{ V, } R_L = 2.0 \text{ k}\Omega$ $V_{CC} = 30 \text{ V, } R_L = 10 \text{ k}\Omega$	V _{OH}	3.3 26 27	3.5 - 28		3.3 26 27	3.5 - 28		3.3 26 27	3.5 - 28	- - -	V
Output Voltage–Low Limit $V_{CC} = 5.0 \text{ V}, R_L = 10 \text{ k}\Omega,$ $T_A = T_{high}$ to T_{low} (Note 4)	V _{OL}	-	5.0	20	-	5.0	20	-	5.0	20	mV
Output Source Current $V_{ID} = +1.0 \text{ V, } V_{CC} = 15 \text{ V}$ $T_A = T_{high} \text{ to } T_{low} \text{ (LM358A Only)}$	I _{O+}	20	40	-	20	40	-	20 10	40 -	- -	mA
Output Sink Current $V_{ID} = -1.0 \text{ V, } V_{CC} = 15 \text{ V}$ $T_A = T_{high} \text{ to } T_{low} \text{ (LM358A Only)}$ $V_{ID} = -1.0 \text{ V, } V_O = 200 \text{ mV}$	I _O –	10 12	20 50	-	10 12	20 50	-	10 5.0 12	20 - 50	- - -	mA mA μA
Output Short Circuit to Ground (Note 6)	I _{SC}	_	40	60	_	40	60	_	40	60	mA
Power Supply Current (Total Device) T _A = T _{high} to T _{low} (Note 4)	I _{CC}			2.0		1.5	2.0		1.5	2.0	mA
$V_{CC} = 30 \text{ V}, V_{O} = 0 \text{ V}, R_{L} = \infty$ $V_{CC} = 5 \text{ V}, V_{O} = 0 \text{ V}, R_{L} = \infty$		_ _	1.5 0.7	3.0 1.2	- -	1.5 0.7	3.0 1.2	- - - 170°	1.5 0.7	2.0 1.2	

^{4.} LM258: T_{low} = -25°C, T_{high} = +85°C LM2904/A/E: T_{low} = -40°C, T_{high} = +105°C NCV2904 is qualified for automotive use.

LM358, LM358A, LM358E: $T_{low} = 0$ °C, $T_{high} = +70$ °C LM2904V & NCV2904: $T_{low} = -40$ °C, $T_{high} = +125$ °C

^{5.} The input common mode voltage or either input signal voltage should not be allowed to go negative by more than 0.3 V. The upper end of the common mode voltage range is V_{CC} – 1.7 V, but either or both inputs can go to +32 V without damage, independent of the magnitude of V_{CC}.

^{6.} Short circuits from the output to V_{CC} can cause excessive heating and eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.

ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V, V_{EE} = Gnd, T_A = 25°C, unless otherwise noted.)

		LM2	904/LM:	2904E	L	M2904	Α	LM2904V, NCV2904			ĺ
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Input Offset Voltage V _{CC} = 5.0 V to 30 V, V _{IC} = 0 V to V _{CC} -1.7 V, V _O 1.4 V, R _S = 0 Ω	V _{IO}										mV
$T_A = 25^{\circ}C$		-	2.0	7.0	-	2.0	7.0	-	-	7.0	
$T_A = T_{high}$ (Note 7)		-	-	10	-	-	10	-	-	13	
$T_A = T_{low}$ (Note 7)		-	_	10	-	-	10	-	-	10	
Average Temperature Coefficient of Input Offset Voltage $T_A = T_{high} \ to \ T_{low} \ (Note \ 7)$	ΔV _{IO} /ΔΤ	-	7.0	-	_	7.0	_	_	7.0	-	μV/°C
Input Offset Current	I_{IO}	_	5.0	50	_	5.0	50	_	5.0	50	nA
$T_A = T_{high}$ to T_{low} (Note 7)		-	45	200	-	45	200	-	45	200	
Input Bias Current	I_{IB}	-	-45	-250	-	-45	-100	-	-45	-250	
$T_A = T_{high}$ to T_{low} (Note 7)		-	-50	-500	-	-50	-250	-	-50	-500	
Average Temperature Coefficient of Input Offset Current	ΔΙ _{ΙΟ} /ΔΤ	-	10	_	-	10	-	-	10	_	pA/°(
$T_A = T_{high}$ to T_{low} (Note 7)											
Input Common Mode Voltage Range (Note 8), V _{CC} = 30 V	V_{ICR}	0	-	28.3	0	-	28.3	0	-	28.3	V
$V_{CC} = 30 \text{ V}, T_A = T_{high} \text{ to } T_{low}$		0	-	28	0	-	28	0	-	28	
Differential Input Voltage Range	V_{IDR}	_	-	V_{CC}	-	-	V_{CC}	-	-	V_{CC}	V
Large Signal Open Loop Voltage Gain	A_{VOL}										V/m\
$R_L = 2.0 \text{ k}\Omega$, $V_{CC} = 15 \text{ V}$, For Large V_O Swing,		25	100	-	25	100	-	25	100	-	
$T_A = T_{high}$ to T_{low} (Note 7)		15	-	-	15	-	-	15	-	-	
Channel Separation $1.0 \text{ kHz} \leq f \leq 20 \text{ kHz, Input Referenced}$	CS	-	-120	-	-	-120	-	-	-120	-	dB
Common Mode Rejection $R_S \leq 10 \; k\Omega$	CMR	50	70	_	50	70	-	50	70	_	dB
Power Supply Rejection	PSR	50	100	_	50	100	-	50	100	_	dB
Output Voltage–High Limit $T_A = T_{high}$ to T_{low} (Note 7) $V_{CC} = 5.0$ V, $R_L = 2.0$ k Ω , $T_A = 25$ °C $V_{CC} = 30$ V, $R_L = 2.0$ k Ω	V _{OH}	3.3 26	3.5		3.3 26	3.5 -	- -	3.3 26	3.5 -		V
$V_{CC} = 30 \text{ V}, R_L = 10 \text{ k}\Omega$		27	28	-	27	28	-	27	28	-	
Output Voltage–Low Limit $ V_{CC} = 5.0 \text{ V, } R_L = 10 \text{ k}\Omega, $ $ T_A = T_{high} \text{ to } T_{low} \text{ (Note 7)} $	V _{OL}	-	5.0	20	-	5.0	20	-	5.0	20	mV
Output Source Current $V_{ID} = +1.0 \text{ V}, V_{CC} = 15 \text{ V}$	I _{O+}	20	40	-	20	40	-	20	40	-	mA
Output Sink Current	I _O _										
$V_{\rm ID}$ = -1.0 V, $V_{\rm CC}$ = 15 V		10	20	-	10	20	-	10	20	-	mA
$V_{\rm ID}$ = -1.0 V, $V_{\rm O}$ = 200 mV		-	-	-	-	-	-	-	-	-	μΑ
Output Short Circuit to Ground (Note 9)	I _{SC}	-	40	60	-	40	60	-	40	60	mA
Power Supply Current (Total Device) TA = T _{high} to T _{low} (Note 7)	I _{CC}										mA
$V_{CC} = 30 \text{ V}, V_O = 0 \text{ V}, R_L = \infty$		_	1.5	3.0	_	1.5	3.0	_	1.5	3.0	
$V_{CC} = 50 \text{ V}, V_0 = 0 \text{ V}, R_L = \infty$		_	0.7	1.2	_	0.7	1.2	_	0.7	1.2	
IM258: T = _25°C T = ±85°C		<u> </u>	I M328V		<u> </u>			<u> </u>			I

^{7.} LM258: T_{low} = -25°C, T_{high} = +85°C LM2904/A/E: T_{low} = -40°C, T_{high} = +105°C NCV2904 is qualified for automotive use.

LM358, LM358A, LM358E: $T_{low} = 0$ °C, $T_{high} = +70$ °C LM2904V & NCV2904: $T_{low} = -40$ °C, $T_{high} = +125$ °C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{8.} The input common mode voltage or either input signal voltage should not be allowed to go negative by more than 0.3 V. The upper end of the common mode voltage range is V_{CC} – 1.7 V, but either or both inputs can go to +32 V without damage, independent of the magnitude of V_{CC}.

^{9.} Short circuits from the output to V_{CC} can cause excessive heating and eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.

CIRCUIT DESCRIPTION

The LM358 series is made using two internally compensated, two-stage operational amplifiers. The first stage of each consists of differential input devices Q20 and Q18 with input buffer transistors Q21 and Q17 and the differential to single ended converter Q3 and Q4. The first stage performs not only the first stage gain function but also performs the level shifting and transconductance reduction functions. By reducing the transconductance, a smaller compensation capacitor (only 5.0 pF) can be employed, thus saving chip area. The transconductance reduction is accomplished by splitting the collectors of Q20 and Q18. Another feature of this input stage is that the input common mode range can include the negative supply or ground, in single supply operation, without saturating either the input devices or the differential to single-ended converter. The second stage consists of a standard current source load amplifier stage.

Each amplifier is biased from an internal-voltage regulator which has a low temperature coefficient thus giving each amplifier good temperature characteristics as well as excellent power supply rejection.

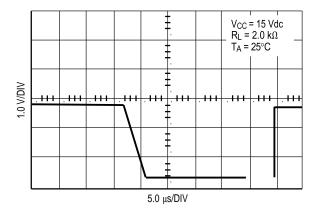
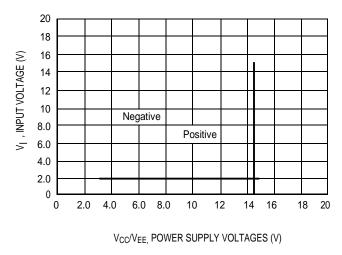


Figure 3. Large Signal Voltage Follower Response





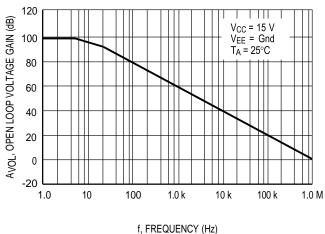
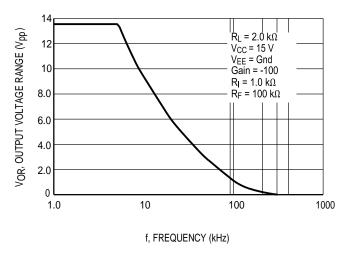


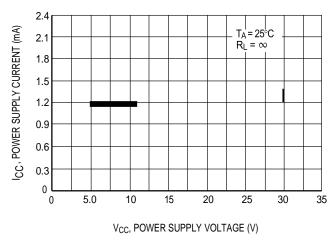
Figure 5. Large-Signal Open Loop Voltage Gain



550 V_{CC} = 30 V 500 450 450 400 350 300 00.250 V_{EE} = Gnd 500 T_A = 25°C C_L = 50 pF Input Output 200 0 0 1.0 2.0 3.0 4.0 5.0 6.0 7.0 8.0 t, TIME (µs)

Figure 6. Large-Signal Frequency Response

Figure 7. Small Signal Voltage Follower Pulse Response (Noninverting)



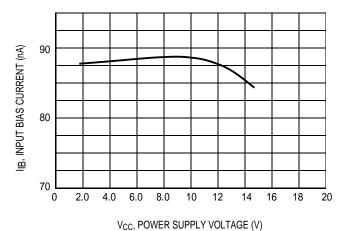


Figure 8. Power Supply Current versus Power Supply Voltage

Figure 9. Input Bias Current versus Supply Voltage

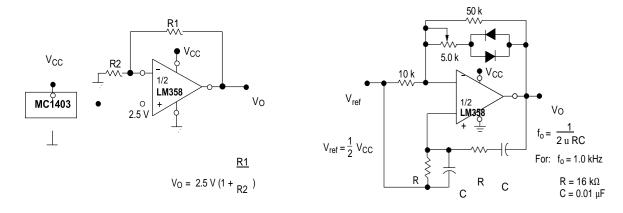


Figure 10. Voltage Reference

Figure 11. Wien Bridge Oscillator

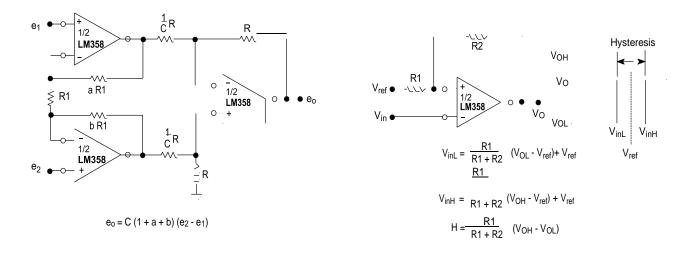
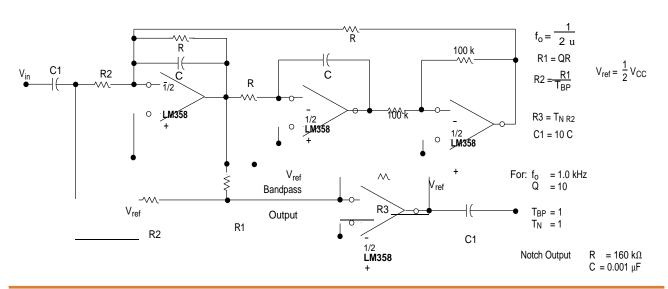
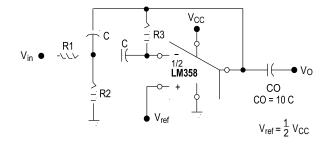


Figure 12. High Impedance Differential Amplifier

Figure 13. Comparator with Hysteresis





Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value
$$f_0$$
, C

Then: $R3 = \frac{Q}{u f_0 C}$
 $R1 = \frac{R3}{2 A(f_0)}$

$$R2 = \frac{R1 R3}{4Q^2 R1 - R^2}$$

For less than 10% error from operational amplifier. $\frac{Q_0 f_0}{BW} < 0.1$

Where fo and BW are expressed in Hz.

If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

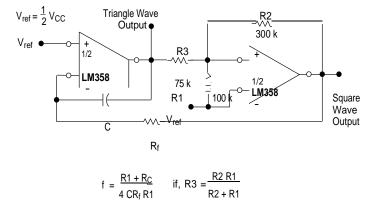


Figure 15. Function Generator

Figure 16. Multiple Feedback Bandpass Filter

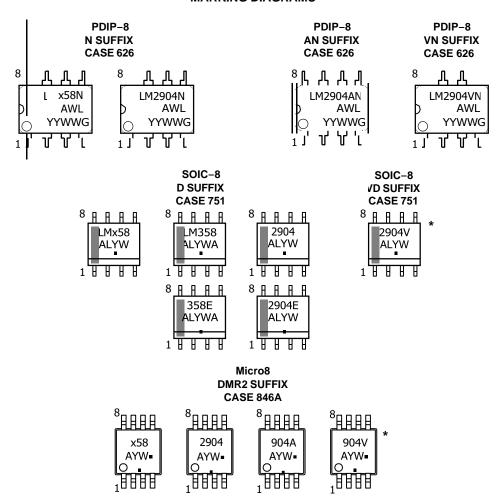
ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping [†]
LM358ADR2G			2500 / Tape & Reel
LM358DG		SOIC-8 (Pb-Free)	98 Units / Rail
LM358DR2G		(IB TICC)	2500 / Tape & Reel
LM358EDR2G	0°C to +70°C	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM358DMR2G		Micro8 (Pb-Free)	4000 / Tape & Reel
LM358NG		PDIP-8 (Pb-Free)	50 Units / Rail
LM258DG		SOIC-8	98 Units / Rail
LM258DR2G		(Pb-Free)	2500 / Tape & Reel
LM258DMR2G	−25°C to +85°C	Micro8 (Pb-Free)	4000 / Tape & Reel
LM258NG		PDIP-8 (Pb-Free)	50 Units / Rail
LM2904DG		SOIC-8 (Pb-Free)	98 Units / Rail
LM2904DR2G			2500 / Tape & Reel
LM2904EDR2G		SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2904DMR2G		Micro8 (Pb-Free)	2500 / Tape & Reel
LM2904NG	-40°C to +105°C	PDIP-8 (Pb-Free)	50 Units / Rail
LM2904ADMG		Micro8	4000 / Tape & Reel
LM2904ADMR2G		(Pb-Free)	4000 / Tape & Reel
LM2904ANG		PDIP-8 (Pb-Free)	50 Units / Rail
LM2904VDG		SOIC-8	98 Units / Rail
LM2904VDR2G		(Pb-Free)	2500 / Tape & Reel
LM2904VDMR2G		Micro8 (Pb-Free)	4000 / Tape & Reel
LM2904VNG	-40°C to +125°C	PDIP-8 (Pb-Free)	50 Units / Rail
NCV2904DR2G*		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2904DMR2G*		Micro8 (Pb-Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MARKING DIAGRAMS



x = 2 or 3

A = Assembly Location

 $\begin{array}{ll} \text{WL, L} &= \text{Wafer Lot} \\ \text{YY, Y} &= \text{Year} \\ \text{WW, W} &= \text{Work Week} \\ \text{G} &= \text{Pb-Free Package} \end{array}$

■ = Pb-Free Package – (Note: Microdot may be in either location)

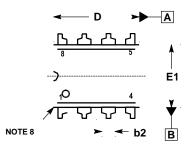
*This diagram also applies to NCV2904

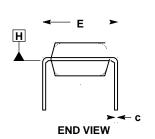
MECHANICAL CASE OUTLINE



PDIP-8 CASE 626-05 ISSUE P

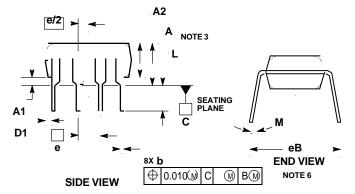
DATE 22 APR 2015





TOP VIEW

WITH LEADS CONSTRAINED NOTE 5



STYLE 1:
PIN 1. AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND 6. OUTPUT7. AUXILIARY 8. V_{CC}

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES.

- DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
- NOT TO EXCEED 0.10 INCH.

 5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C
- DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE
- LEADS, WHERE THE LEADS EXIT THE BODY.
- 8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060		1.52	
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100) BSC	2.54	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX = Assembly Location

= Wafer Lot WL = Year YY ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " •", may or may not be present.

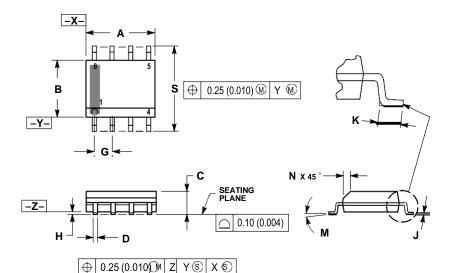
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SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011

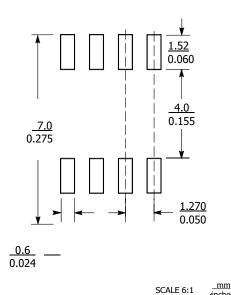


NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

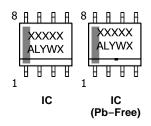
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

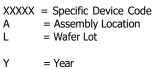
SOLDERING FOOTPRINT*



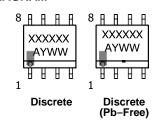
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*





= Work Week W = Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location = Year

WW = Work Week = Pb-Free Package

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14:	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE	PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	8. N-DRAIN STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
5. DRAIN 6. DRAIN 7. DRAIN 7. DRAIN 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6 STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: PIN 1. BASE, DIE #1	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

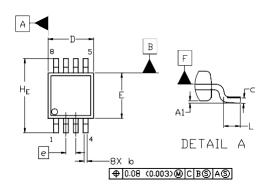
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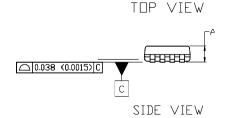
Micro8 CASE 846A-02 ISSUE K

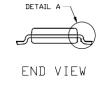
DATE 16 JUL 2020



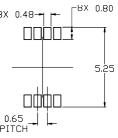
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- 5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.





NDTE 3



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy an soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS				
ויונת	MIN.	N□M₋	MAX.		
A			1.10		
A1	0.05	0.08	0.15		
Ø	0.25	0.33	0-40		
U	0.13	0.18	0.23		
D	2.90	3.00	3.10		
E	2.90	3.00	3.10		
е	0.65 BSC				
HE	4.75	4.90	5.05		
١	0.40	0.55	0.70		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device CodeA = Assembly Location

Y = Year W = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
SOURCE	2. GATE 1	2. N-GATE
SOURCE	3. SOURCE 2	P-SOURCE
4. GATE	4. GATE 2	4. P-GATE
5. DRAIN	5. DRAIN 2	5. P-DRAIN
6. DRAIN	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8 DRAIN	8 DRAIN 1	8 N-DRAIN

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